

AO4601

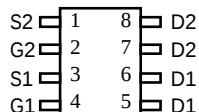
Complementary Enhancement Mode Field Effect Transistor

General Description

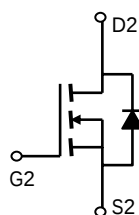
The AO4601 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications. *Standard Product AO4601 is Pb-free (meets ROHS & Sony 259 specifications). AO4601L is a Green Product ordering option. AO4601 and AO4601L are*

Features

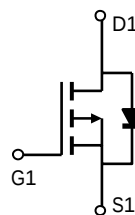
n-channel	p-channel
V_{DS} (V) = 30V	-30V
I_D = 4.7A ($V_{GS}=10V$)	-8A ($V_{GS} = -20V$)
$R_{DS(ON)}$	$R_{DS(ON)}$
< 55m Ω ($V_{GS}=10V$)	< 18m Ω ($V_{GS} = -20V$)
< 70m Ω ($V_{GS}=4.5V$)	< 19m Ω ($V_{GS} = -10V$)
< 110m Ω ($V_{GS} = 2.5V$)	



SOIC-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 12	± 25	V
Continuous Drain Current ^A	I_D	4.7	-8	A
		4	-6.9	
Pulsed Drain Current ^B	I_{DM}	30	-50	
Power Dissipation	P_D	2	2	W
		1.44	1.44	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch	52	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		n-ch	78	110	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	n-ch	48	60	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	50	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		p-ch	73	110	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	p-ch	31	40	$^\circ\text{C/W}$

n-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.6	1	1.4	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	10			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4A T _J =125°C		45 66	55 80	mΩ
		V _{GS} =4.5V, I _D =3A		55	70	mΩ
		V _{GS} =2.5V, I _D =2A		83	110	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4A		8		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.8	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		390		pF
C _{oss}	Output Capacitance			54.5		pF
C _{rss}	Reverse Transfer Capacitance			41		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =4A		0.6		nC
Q _{gs}	Gate Source Charge			1.38		nC
Q _{gd}	Gate Drain Charge			4.34		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =3.75Ω, R _{GEN} =6Ω		3.3		ns
t _r	Turn-On Rise Time			1		ns
t _{D(off)}	Turn-Off DelayTime			21.7		ns
t _f	Turn-Off Fall Time			2.1		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4A, dI/dt=100A/μs		12		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4A, dI/dt=100A/μs		6.3		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 3 : Sept 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

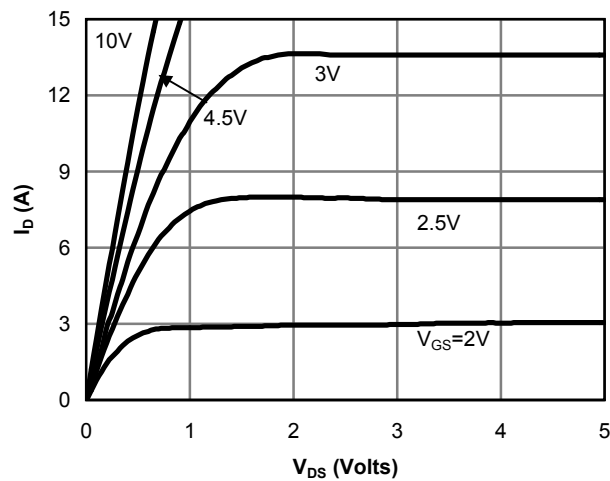


Fig 1: On-Region Characteristics

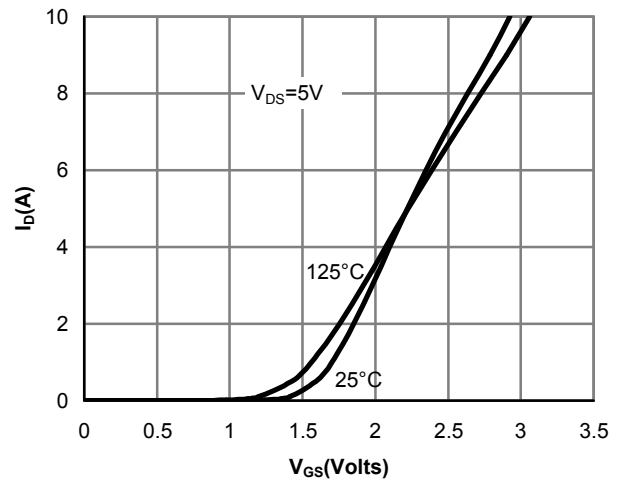


Figure 2: Transfer Characteristics

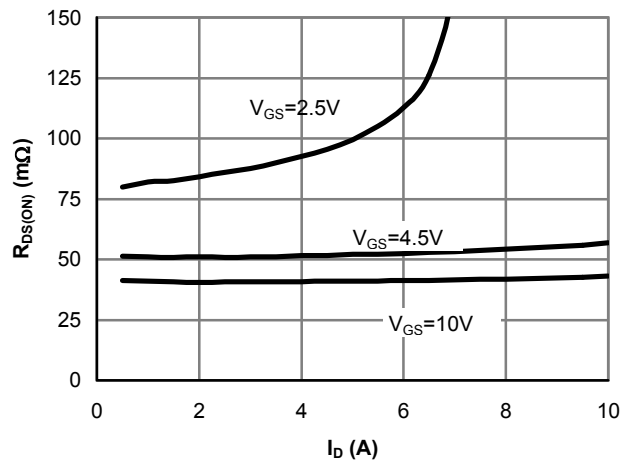


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

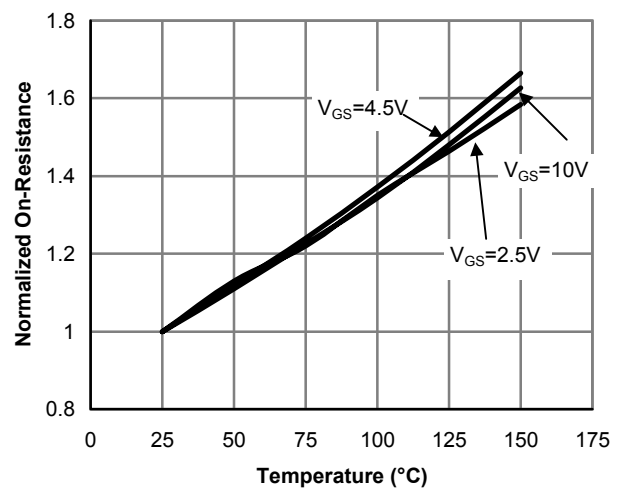


Figure 4: On-Resistance vs. Junction Temperature

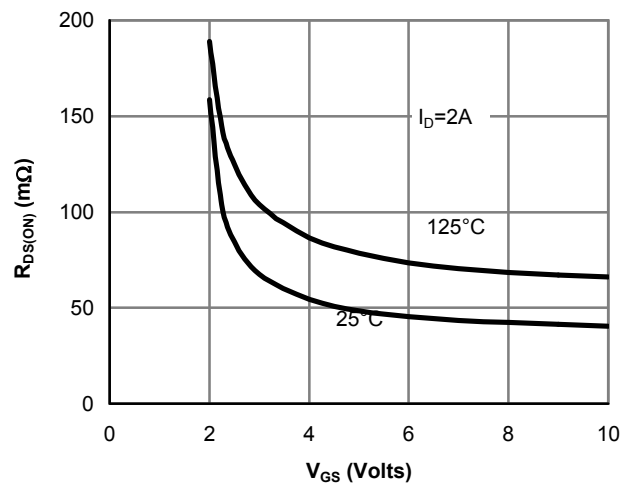


Figure 5: On-Resistance vs. Gate-Source Voltage

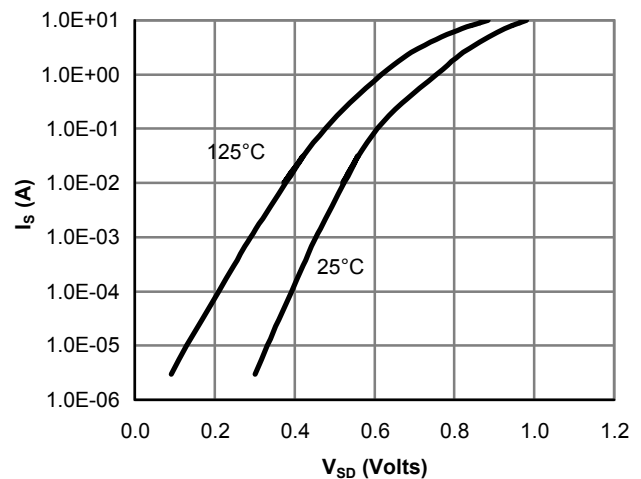


Figure 6: Body-Diode Characteristics

N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

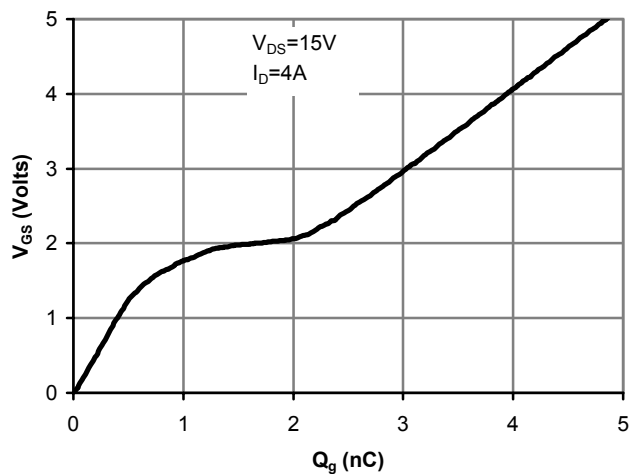


Figure 7: Gate-Charge Characteristics

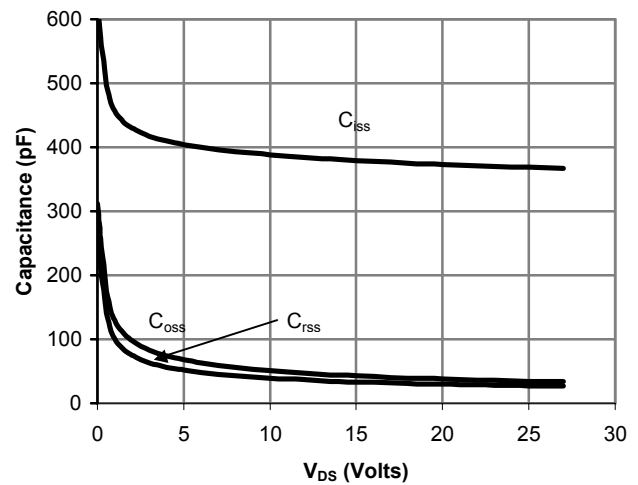


Figure 8: Capacitance Characteristics

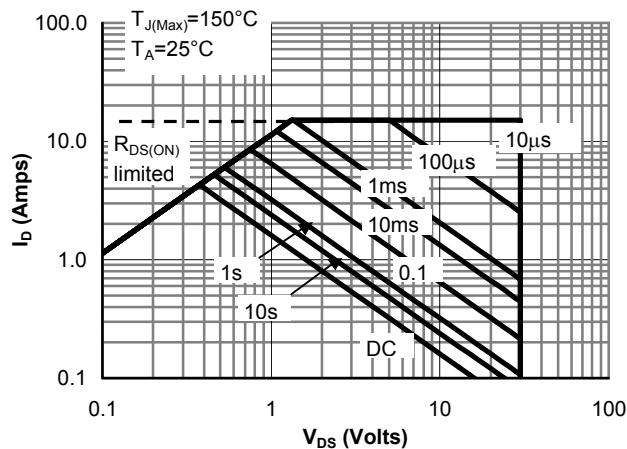


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

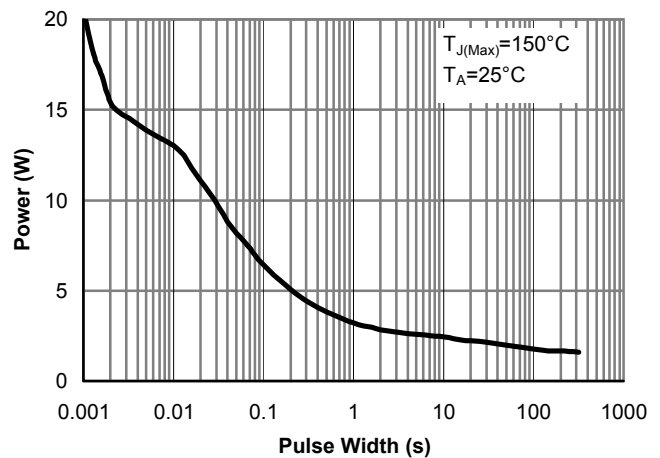


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

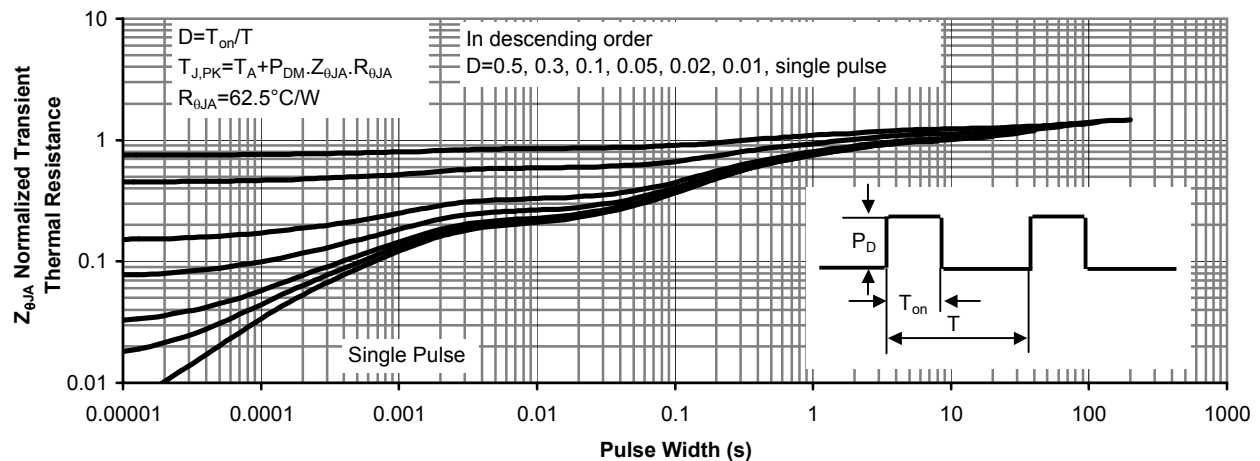


Figure 11: Normalized Maximum Transient Thermal Impedance

p-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±25V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1.7	-2.5	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	40			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-8A T _J =125°C		16 20.5	19 25	mΩ
		V _{GS} =-20V, I _D =-8A		15	18	mΩ
		V _{GS} =-4.5V, I _D =-5A		33		mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-8A	16	21		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.75	-1	V
I _S	Maximum Body-Diode Continuous Current				-2.6	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		2076		pF
C _{oss}	Output Capacitance			503		pF
C _{rss}	Reverse Transfer Capacitance			302		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-8A		39		nC
Q _{gs}	Gate Source Charge			8		nC
Q _{gd}	Gate Drain Charge			11.4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =1.8Ω, R _{GEN} =3Ω		12.7		ns
t _r	Turn-On Rise Time			7		ns
t _{D(off)}	Turn-Off DelayTime			25.2		ns
t _f	Turn-Off Fall Time			12		ns
t _{rr}	Body Diode Reverse Recovery Time			32		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-8A, dI/dt=100A/μs		26		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 3 : Sept 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

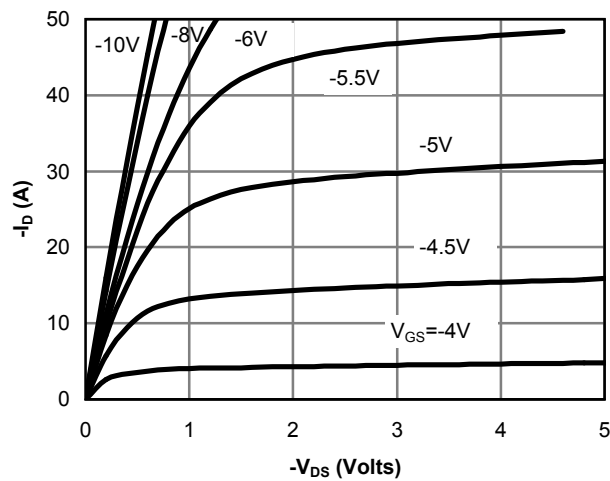


Fig 1: On-Region Characteristics

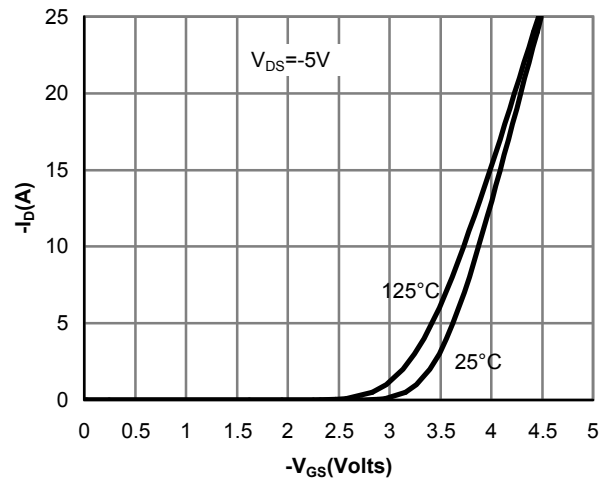


Figure 2: Transfer Characteristics

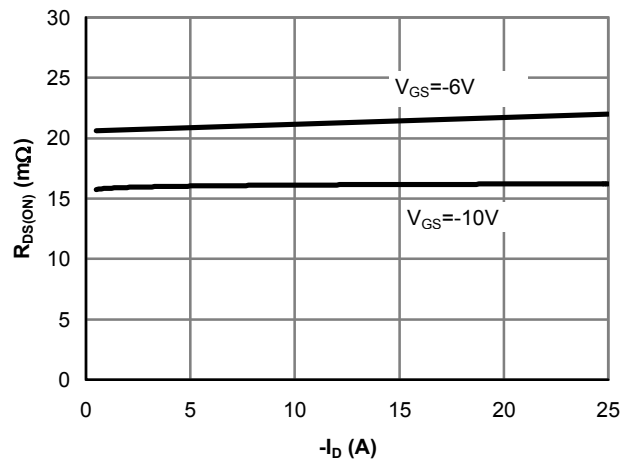


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

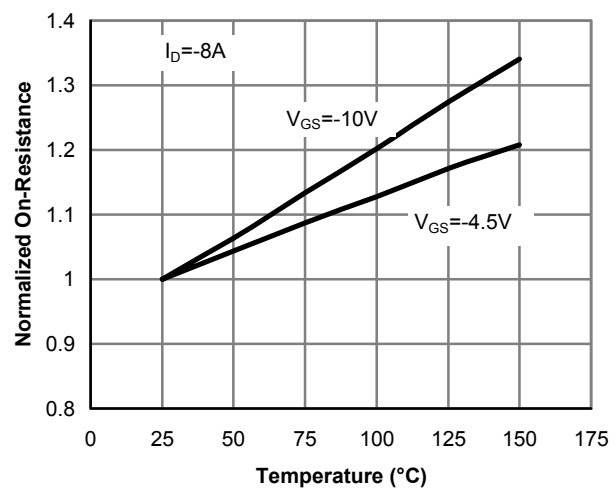


Figure 4: On-Resistance vs. Junction Temperature

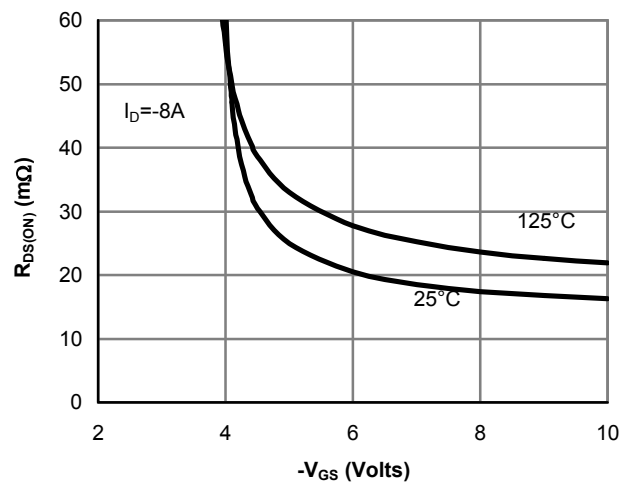


Figure 5: On-Resistance vs. Gate-Source Voltage

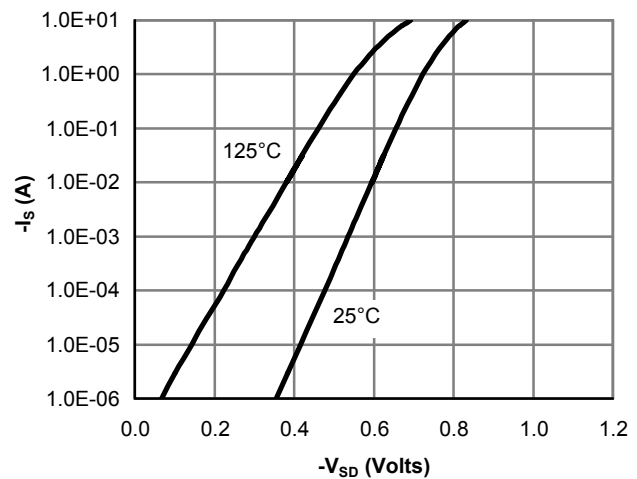


Figure 6: Body-Diode Characteristics

P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

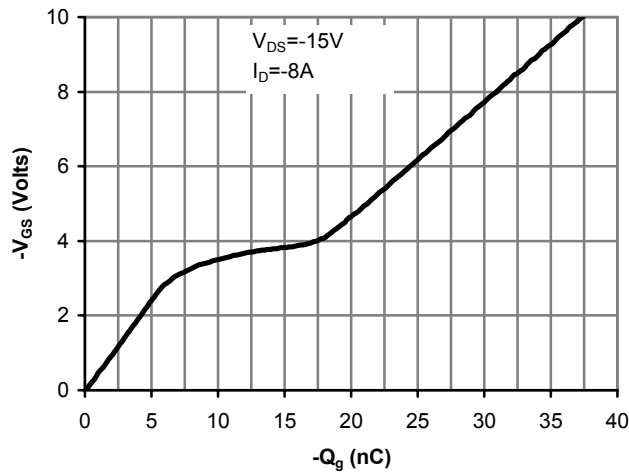


Figure 7: Gate-Charge Characteristics

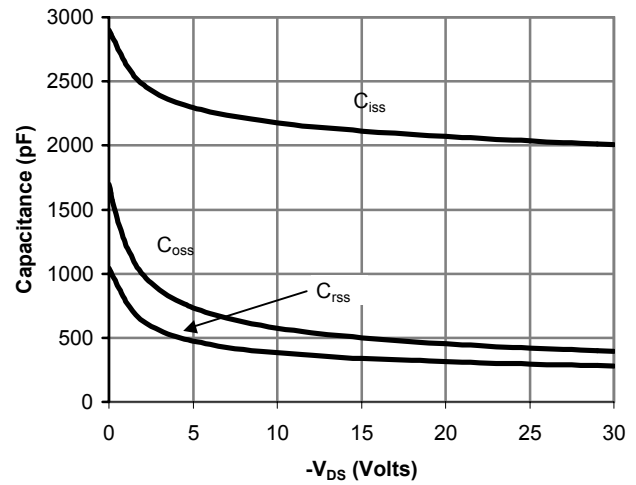


Figure 8: Capacitance Characteristics

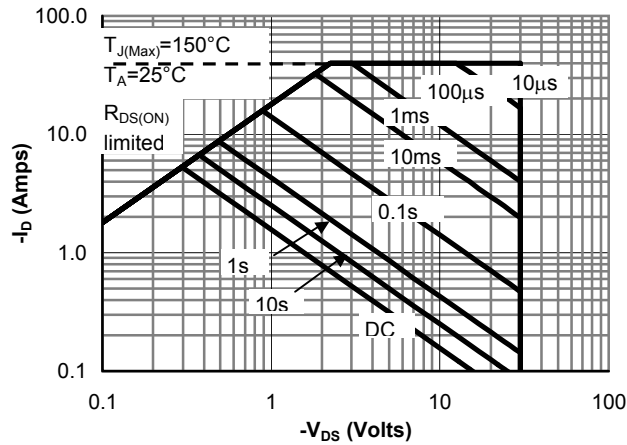


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

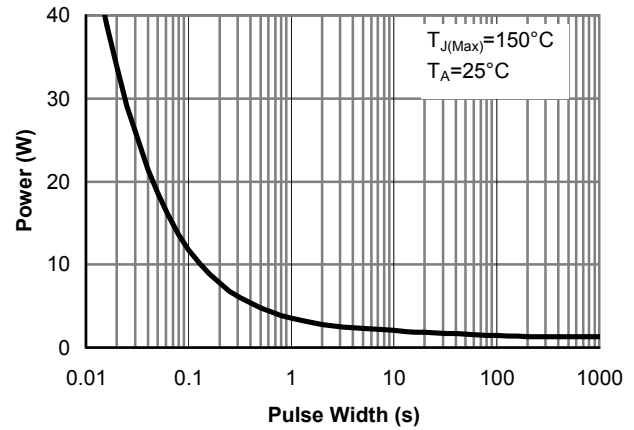


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

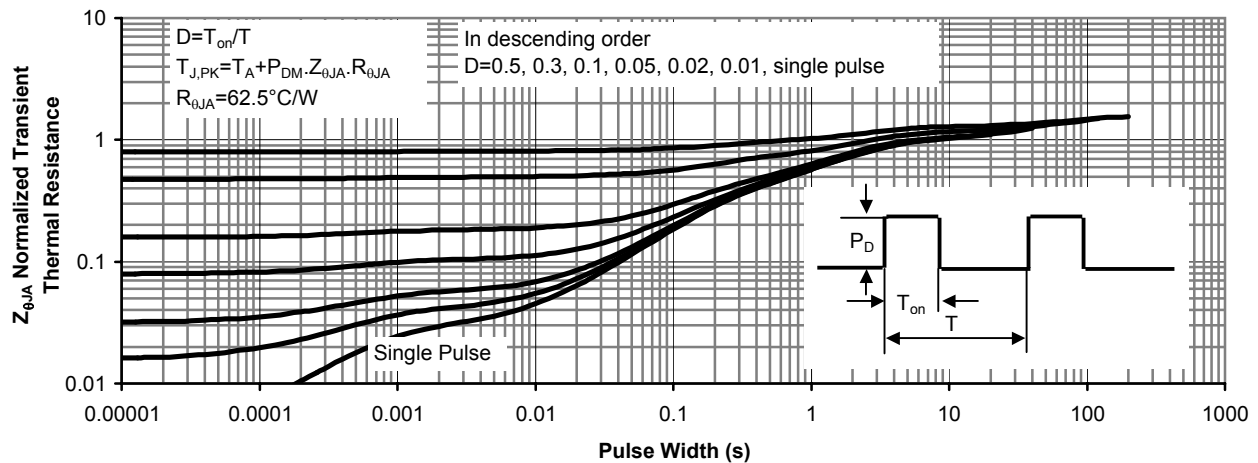


Figure 11: Normalized Maximum Transient Thermal Impedance